1969–Volume 116

Author and Subject Index

Journal of The Electrochemical Society

THE COMPUTER-DERIVED 1969 *JOURNAL* INDEX

The Publication Committee of the Society recommended the use of a computer-derived index in 1968 and this practice is being continued in 1969 and is planned to be in use in future years. Many other technical societies, such as ACS and the American Institute of Physics, are using the same procedure. This index is published two months earlier than the usual index and makes possible indexing more information than before. In this 1969 index, the format is slightly different than in the preceding year. There are two separate author and subject indices: the first set refers only to full-length Journal articles, notes, communications and reviews; the second set refers only to 100-word paper abstracts and recent newspaper abstracts presented at our Spring and Fall National meetings.

USING THE INDEX

To save look-up time, use a search pattern such as:

1. Given any author, go directly to his name in the author and title index to find the full paper title with a page citation or to find a cross reference to the primary author.

2. Given any topic, go to the subject index and first search for the keyword itself; then look under author variants.

keyword	*see also*
Zinc-Silver oxide	Silver oxide-Zinc Silver-Zinc Ag-Zn AgO-Zn Zn-AgO Zn-Ag

3. For detailed explanation of symbols and abbreviations, see the sample pages before each author and title index and subject index.

COMPUTER INDEX LIMITATIONS

Computer indexing in its present state of development has some limits depending on the exact programming:

a. Chemical formulae cannot be reproduced directly because the conventional print-out appears in capital letters only. For example, BI3 may be three atoms of bismuth or boron triiodide. Only the context will determine the true meaning. Where possible an attempt has been made to write out chemical formulae.
b. Superscripts and subscripts appear on the same line immediately following the word to which they refer. Where superscripts and subscripts both appear, the superscript comes after the element symbol. Two atoms of carbon 13 thus appear as C13/2.
c. An author always is listed with all available initials, which to conserve space sometimes can mean omission of one letter or two from the end of his last name.

The Publication Committee will appreciate comments on the usefulness and accuracy of this index, and these comments will be considered seriously in the search for improved indexing methods.

Newton Schwartz
Mario Banus
Ad Hoc Committee
on Indexing

December 1969

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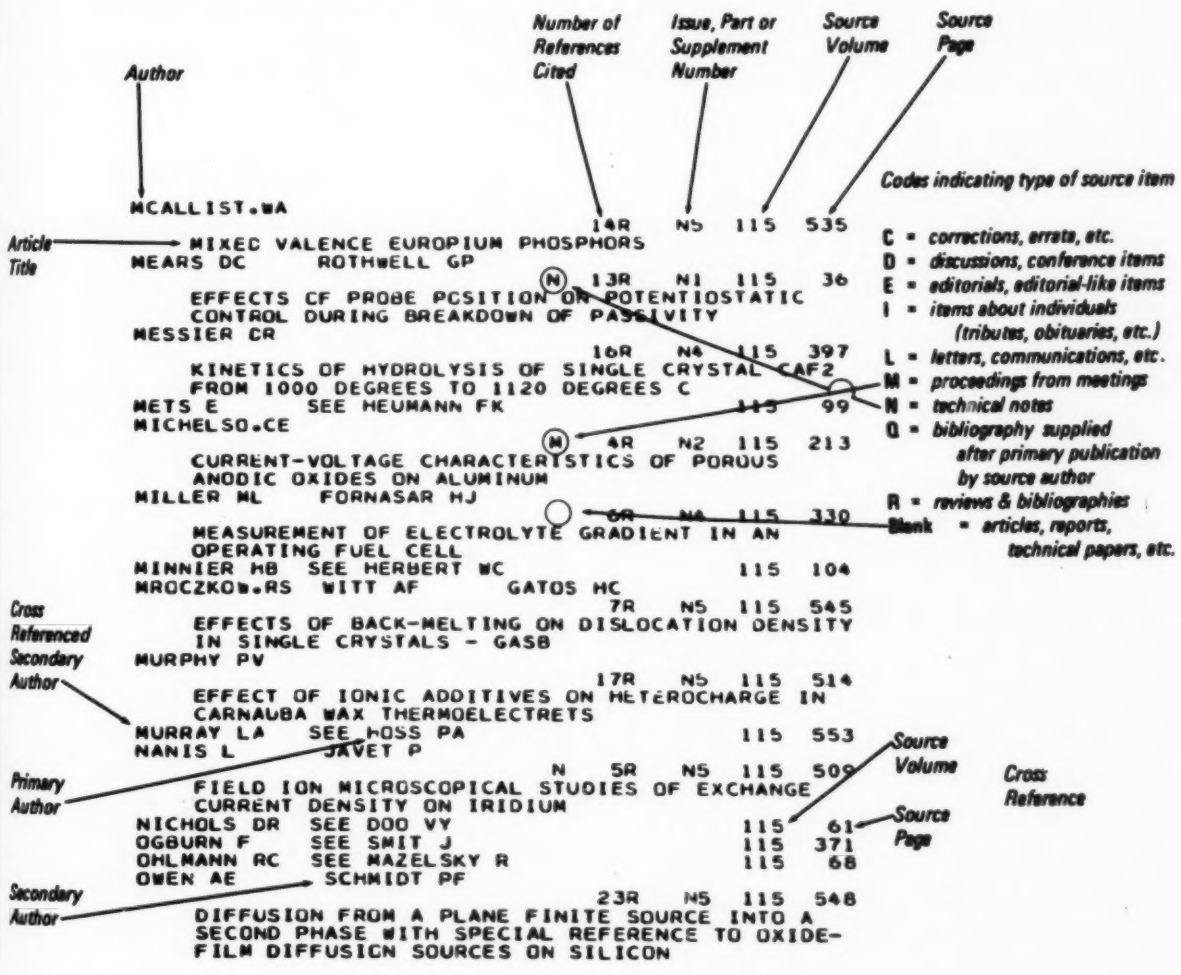
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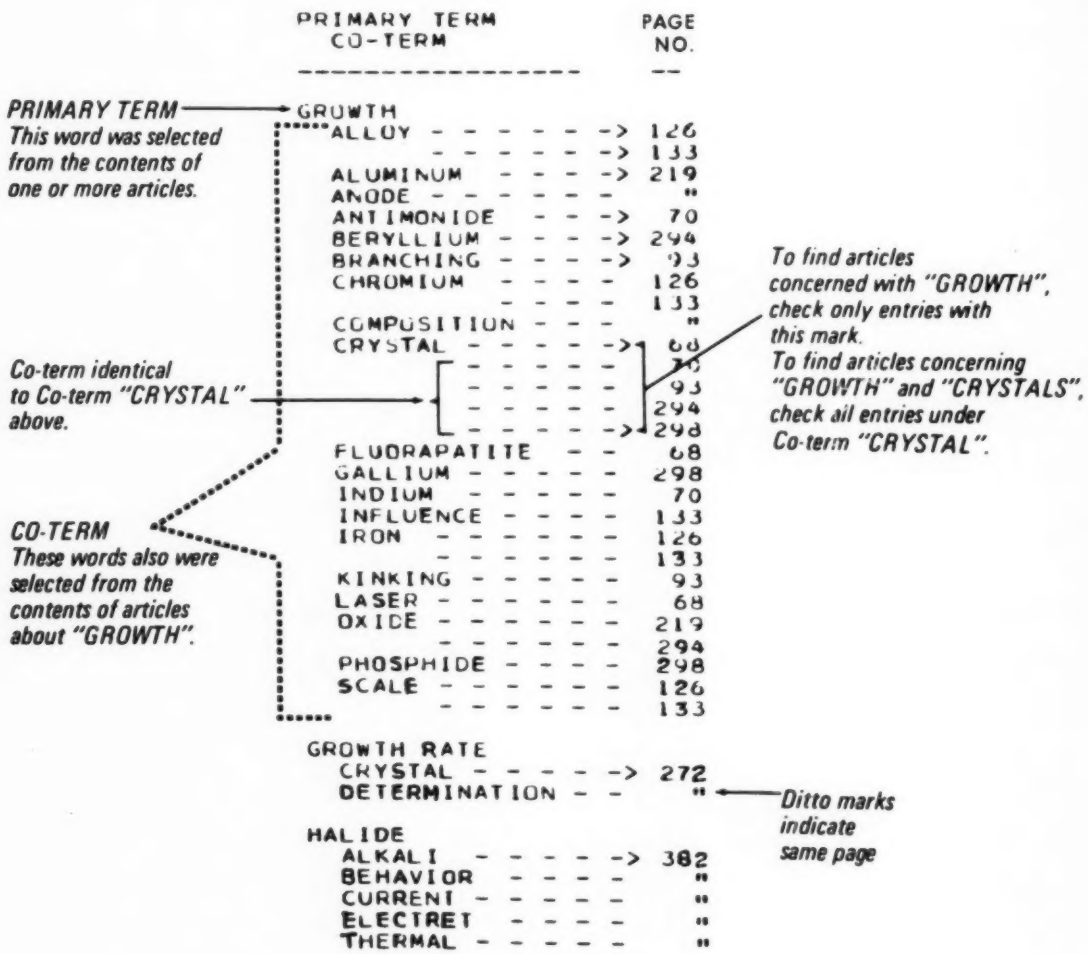

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MEETING ABSTRACT

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To Find Articles on a Specific Topic:

1. Locate any one of the words (Primary Terms) that describes the topic. If you want every title that includes that primary term, select only the articles marked with an arrow (→). This eliminates unnecessary lookups.
2. To narrow selection, use any of the other words (Co-Terms) listed below that Primary Term. When using co-terms always disregard arrows.
3. The PAGE No. refers to the page in the Journal on which the abstract containing the keyword appears. The ABST. No. refers to the abstract number on the cited page number since many abstracts are printed on any one page.

PRIMARY TERM — This word was selected from the contents of one or more articles.

CO-TERM — These words also were selected from the contents of articles about "GROWTH".

Co-term identical to Co-term "CRYSTAL" above.

To find articles concerned with "GROWTH", check only entries with this mark.

To find articles concerning "GROWTH" and "CRYSTALS", check all entries under Co-term "CRYSTAL".

Ditto marks indicate same page

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CALCIUM - - - - -	"	"
HALOPHOSPHATE - -	"	"
STUDIES - - - - -	"	"
ULTRAVIOLET - - -	"	"
VOLTAMMETRY		
A-C IMPEDANCE - ->140C		236
CHLORIDE - - - ->302C		201
CYCLIC - - - - ->129C		135
- - - - - 140C		236
ELECTROPOLY- - -	129C	135
ETHYLENES - - - -	"	"
IR COMPENSATION -	140C	236
LINEAR SWEEP - -	302C	201
LITHIUM CHLORIDE	"	"
MERIZATION - - -	129C	135
PHENYL- - - - - -	"	"
POTASSIUM - - - -	302C	201
SUBSTITUTED - - -	129C	135
WAFER		
DEVICE - - - - ->251C		368
SILICON - - - - -	"	"
WARPAGE - - - - -	"	"
WAFERS		
BOWING - - - - ->124C		97
SILICON - - - - -	"	"
WARPAGE		
DEVICE - - - - ->251C		368
SILICON - - - - -	"	"
WAFER - - - - - -	"	"
WATER		
CONTAMINATION - ->126C		113
ELECTRON-DONORS ->126C		112
SILICON - - - -	"	"
- - - - - 126C		113
SURFACE CHARGE - 126C		112
THERMAL OXIDE - - 126C		113
WUSTITE		
ELECTRICAL - - ->293C		117
PROPERTIES - - -	"	"
X-RAY		
ALKALINE SOLUTION>281C		22
CADMIUM - - - - -	"	"
ELECTRODES - - -	"	"
FABRICATION - - ->125C		105
FLUORESCENCE - -	"	"
- - ->248C		332
FLUORIDE - - - -	"	"
MICROELECTRONICS 125C		105
RARE EARTH - - - 248C		332
TOPOGRAPHS - - ->125C		103
TRACE ANALYSIS - 248C		332
VIDEO IMAGING - - 125C		103
X-RAY SCANNING		
DEFECTS - - - - ->125C		104
SILICON - - - - -	"	"
SURFACE LAYER - -	"	"
X-RAYS		
DIELECTRIC FILM ->119C		48
STRUCTURE - - - -	"	"
YLIDS		
ELECTROOXIDATION >131C		158
YTTERBIUM		
ALKALINE EARTH ->121C		62
CHLORIDE - - - ->135C		190
DIVALENT - - - - 121C		62
ELECTRODE - - - - 135C		190
EUROPIUM - - - -	"	"
FLUORESCENCE - - 121C		62
LITHIUM CHLORIDE 135C		190
OXYANIONS - - - - 121C		62
POTASSIUM - - - - 135C		190
POTENTIALS - - -	"	"
SAMARIUM - - - -	"	"
YTTRIA		
BROAD EMISSION ->122C		75
ENERGY TRANSFER ->122C		69
EUROPIUM - - - -	"	"
EUROPIUM TO - - -	"	"
EXCITATION BANDS 122C		75
YTTRIUM VANADATE	"	"
YTTRIUM PHOSPHATE		
-VANADATE - - - ->122C		72
- - - ->122C		76
LIFETIME - - - -	"	"
LUMINESCENCE - -	"	"
- ->248C		328
TERBIUM PLUS- - - 122C		72
THREE - - - - - -	"	"
VANADATE - - - - 122C		76
YTTRIUM VANADATE 248C		328
YTTRIUM VANADATE		
ACTIVATION - - ->251C		371
BROAD EMISSION ->122C		75
DOPING - - - - ->122C		74
EUROPIUM - - - -	"	"
EXCITATION BANDS 122C		75
LUMINESCENCE - ->248C		328
PHOSPHOR - - - - 122C		74
SILICON - - - - -	"	"
YTTRIA - - - - - 122C		75
YTTRIUM PHOSPHATE 248C		328
ZEOLITES		
ION EXCHANGE - ->138C		217
PRINCIPLES - - -	"	"
ZINC		
ALKALINE - - - ->280C		15
- - - ->280C		16
ZINC (CONTD)		
ALKALINE - - - ->140C		239
ALKALINE ZINCATE >280C		18
>281C		19
ALLOYS - - - - - ->289C		83
ANODIC - - - - - 140C		239
- - - - ->141C		240
CADMIUM - - - - ->127C		118
- - - - - 141C		240
CALCIUM HYDROXIDE>280C		17
CHLORIDE - - - ->283C		36
COPPER - - - - - 289C		83
CURRENT DENSITY ->281C		24
DEPOSITION - - ->280C		14
- - - 280C		15
DISCHARGE - - - 281C		24
DISSOLUTION - - - 280C		14
- - - 289C		83
- - ->140C		238
- - - 140C		239
- - - 141C		240
EFFICIENCY - - - 281C		24
ELECTROCHEMICAL - 280C		16
ELECTROCRYSTALLIZ 280C		18
ELECTRODE - - - - 289C		83
ELECTRODEPOSITION 283C		36
ELECTRODES - - - 280C		17
ELECTRODISSOLUTIO 283C		36
ELECTROLYTES - - 280C		16
KINETICS - - - - 283C		36
KOH - - - - - - - 140C		238
OXIDATION - - - - 280C		16
PASSIVATION - - - 140C		238
POROUS - - - - - 281C		24
POTENTIAL - - - - 281C		19
- - - - 289C		83
SILVER - - - - - 141C		240
SOLUTIONS - - - - 280C		15
- - - - 280C		18
- - - - 281C		19
TELLURIUM - - - - 127C		118
TERNARY SYSTEM -	"	"
ZINC ELECTRODES		
CHARGE - - - - ->280C		13
CONSTANT CURRENT	"	"
DISCHARGE - - - -	"	"
ZINC SULFIDE		
ELECTROLUMINESCEN>124C		92
ZINC TELLURIDE		
ION-IMPLANTED - ->299C		168
OXYGEN - - - - -	"	"
PHOTOLUMINESCENCE	"	"
ZIRCONIA		
DIFFUSION - - - ->293C		122
ELECTROLYTE CELLS>303C		208
OXYGEN - - - - - 293C		122
OXYGEN ISOTOPE - 303C		208
ZIRCONIUM		
ALUMINIUM - - - ->117C		26
ALUMINUM - - - ->136C		202
ANODIC OXIDE - ->118C		30
ANODIZATION - - - 117C		26
BERYLLIUM - - - -	"	"
- - - ->135C		195
COUPLE - - - - -	"	"
DIFLUORIDE - - - 136C		202
EVOLUTION - - -	"	"
FILM - - - - - - 118C		30
FLUORIDE - - - - 135C		195
- - - -	"	"
GROWTH - - - - - 118C		30
HYDROGEN - - - - 136C		202
LITHIUM FLUORIDE 135C		195
OVERVOLTAGE - - - 136C		202
POTASSIUM - - - -	"	"
SOLID STATE - - - 117C		26
URANIUM - - - - - 135C		195
ZIRCONIUM DIOXIDE		
FLUORESCENCE - ->124C		89
PENTOXIDE - - - -	"	"
PHASE EQUILIBRIA	"	"
PHOSPHOROUS - - -	"	"
STRONTIUM OXIDE -	"	"
TIN OXIDE - - - -	"	"
1,2-DIACTIVATED		
COUPLING - - - ->129C		137
ELECTROLYTIC - -	"	"